

Specifications	
Part Number	IXFN24N100F
Manufacturer	IXYS RF
Description	MOSFET N-CH 1000V 24A SOT227B
Category	Discrete Semiconductor Products > Transistors - FETs,
Part Status	4 pcs Stock
Manufacturer Standard Lead Time	14 Weeks
Detailed Description	N-Channel 1000V 24A (Tc) 600W (Tc) Chassis Mount
Series	HiPerRF™
Technology	MOSFET (Metal Oxide)
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Chassis Mount
Package / Case	SOT-227-4, miniBLOC
Supplier Device Package	SOT-227B
Power Dissipation (Max)	600W (Tc)
FET Type	N-Channel
FET Feature	-
Drain to Source Voltage (Vdss)	1000V
Current - Continuous Drain (Id) @ 25°C	24A (Tc)
Rds On (Max) @ Id, Vgs	390 mOhm @ 12A, 10V
Vgs(th) (Max) @ Id	5.5V @ 8mA
Gate Charge (Qg) (Max) @ Vgs	195nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	6600pF @ 25V
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Packaging	Tube
Lead Free Status / RoHS Status	Lead free / RoHS Compliant
Moisture Sensitivity Level (MSL)	1 (Unlimited)

In:

Not Actual Photo
IXYS International Co., Limited.

IXFN250N06
IXYS
IGBT Modules



IXFN23N100
IXYS Corporation
MOSFET N-CH 1000V 23A SOT-
227B



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IXFN25N80
IXYS
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IXFN240N25X3
IXYS Corporation
MOSFET N-CH 250V 240A
SOT227B



IXFN24N100F
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MOSFET N-CH 1KV 24A SOT227B



IXFN24N100
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MOSFET N-CH 1KV 24A SOT-227B

More

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